

Form PTO-1449	ATTY DOCKET NO. 0020-5123P	APPLICATION NO. NEW - Div. of 09/714,143
<b>INFORMATION DISCLOSURE CITATION IN AN APPLICATION</b> (Use several sheets if necessary)	APPLICANT S. NAGAHAMA et al.	
	FILING DATE June 24, 2003	GROUP Unassigned

**U.S. PATENT DOCUMENTS**

EXAMINER INITIAL	DOCUMENT NUMBER	Kind	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
du	US 5,146,465	A	1992-09-08	Khan et al.			
	US 5,306,662	A	1994-04-26	Nakamura et al.			
	US 5,747,827	A	1998-05-05	Duggan et al.			
	US 6,377,596	B1	2002-04-23	Tanaka et al.			
	US 5,005,057		1991-04-02	Izumiya et al.			
	US 5,903,017	A	1999-05-11	Itaya et al.			
	US 5,585,648	A	1996-12-17	Tischler			
du	US 5,592,501	A	1997-01-07	Edmond et al.			
	US						

**FOREIGN PATENT DOCUMENTS**

	Office	DOCUMENT NUMBER	Kind	DATE	COUNTRY	CLASS	SUB CLASS	TRANSLATION	
								YES	NO
du	JP	9-116234	A	1997-05-02	JAPAN			abs	
du	JP	2-288371	A	1990-11-28	JAPAN			abs	

**OTHER DOCUMENTS**

(Include Name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.) date, page(s), volume-issue number(s), publisher, city and/or country where published.

du	S. NAKAMURA et al., "Present Status of InGaN/GaN/AlGaIn-Based Laser Diodes," Proceedings of the Second International Conference on Nitride Semiconductors (ICNS '97), 1997, p. 444-446.
	T. SHIBATA et al., "Hydride Vapor Phase Epitaxy Growth of High Quality GaN Bulk Single Crystal by Epitaxial Lateral Overgrowth," Proceedings of the Second International Conference on Nitride Semiconductors (ICNS '97), 1997, pp. 154-155.
	H. MATSUSHIMA et al., "Sub-micron Fine Structure of GaN by MOVPE Selective Area Growth (SAG) and Buried Structure by Epitaxial Lateral Overgrowth (ELO)," Proceedings of the Second International Conference of Nitride Semiconductors (ICNS '97), pp. 492-493.
du	S. NAKAMURA et al., "InGaIn-Based Multi-Quantum-Well-Structure Laser Diodes," Jpn. J. Appl. Phys., Vol. 35 (1996), pp. L74-L76, Part 2, No. 1B, 1/15/1996S.

EXAMINER O. deSil	DATE CONSIDERED 7/2/04
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								YES	NO
<i>add</i> <i>1</i> <i>all</i>	GB	2 298 735	A	1996-09-11	GREAT BRITAIN			X	
	WO	97/11518	A1	1997-03-27	WIPO			abs	
	JP	8-250810	A	1996-09-27	JAPAN			abs	
	JP	10-93194	A	1998-04-10	JAPAN			abs	
	JP	10-145004	A	1998-05-29	JAPAN			abs	

  

OTHER DOCUMENTS	
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<i>add</i>	NAKAMURA et al., "In GaN-Based Multi-Quantum-Well-Structure Laser Diodes with Cleaved Mirror Cavity Facets," Jpn. J. Appl. Phys., Vol. 35 (1996), pp. L217-L220, Part 2, No. 2B, 2/15/1996.
<i>1</i>	S. NAKAMURA et al., "High-Power, Long-Lifetime InGaN Multi-Quantum-Well-Structure Laser Diodes," Jpn. J. Appl. Phys., Vol. 36 (1997), pp. L1059-L1061, Part 2, No. 8B, 8/15/1997.
<i>1</i>	F.L. DEGERTEKIN et al., "Single mode Lamb wave excitation in thin plates by Hertzian contacts," Appl. Phys. Lett. 69 (2), pp. 146-148, 7/8/1996.
<i>1</i>	M. SHAO et al., "Radio-frequency...", Appl. Phys. Lett. 69 (2), pp. 3045-3047, 11/11/1996.
<i>1</i>	S. NAKAMURA et al., "Room-temperature continuous-wave operation of InGaN multi-quantum-well structure laser diodes," Appl. Phys. Lett. 69 (2), pp. 4056-4058, 12/23/1996.
<i>1</i>	SUEMUNE, Ikuo, "Doping in a superlattice structure: Improved hole activation in wide-gap II-VI materials," J. Appl. Phys. Vol. 67, No. 5 (March 1, 1990), pp. 2364-2369.
<i>all</i>	M.A. KHAN, et al., "Reflective filters based on single-crystal GaN/Al <sub>x</sub> Ga <sub>1-x</sub> N multilayers deposited using low-pressure metalorganic chemical vapor deposition," Appl. Phys. Lett. 59 (12), pp. 1449-1451, Sept. 16, 1991.

  

EXAMINER <i>O. Wil</i>	DATE CONSIDERED <i>9/8/04</i>
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	Office	DOCUMENT NUMBER	Kind	DATE	COUNTRY	CLASS	SUB CLASS	TRANSLATION	
								YES	NO
one	JP	5-110138	A	1993-04-30	JAPAN			X	
	JP	5-110139	A	1993-04-30	JAPAN			X	
	JP	5-183189	A	1993-07-23	JAPAN			X	
	JP	6-021511	A	1994-01-28	JAPAN			X	
	JP	6-268257	A	1994-09-22	JAPAN			X	
	JP	8-228048	A	1996-09-03	JAPAN			X	
	JP	9-116234	A	1997-05-02	JAPAN			X	
	JP	9-148678	A	1997-06-06	JAPAN			X	
	JP	7-169701	A	1995-07-04	JAPAN			X	
	JP	8-023124	A	1996-01-23	JAPAN			X	
	JP	8-056015	A	1996-02-27	JAPAN			X	
	JP	8-203834	A	1996-08-09	JAPAN			X	
	JP	9-232629	A	1997-09-05	JAPAN			X	
	JP	9-293935	A	1997-11-11	JAPAN			X	
	JP	9-298341	A	1997-11-18	JAPAN			X	
one	JP	8-070139	A	1996-03-12	JAPAN			X	

**OTHER DOCUMENTS** (Include Name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.) date, page(s), volume-issue number(s), publisher, city and/or country where published.)


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ATTY. DOCKET NO.  
0020-5123PAPPLICATION NO.  
10/601,582 ✓APPLICANT  
Shinichi NAGAHAMA et al.FILING DATE  
June 24, 2003GROUP  
2815

## U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	Kind	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
<i>Q.W.</i>	US 5,578,839	A	1996-11-26	Nakamura et al.			
<i>Q.W.</i>	US 5,583,879	A	1996-12-10	Yamazaki et al.			
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## FOREIGN PATENT DOCUMENTS

	Office	DOCUMENT NUMBER	Kind	DATE	COUNTRY	CLASS	SUB CLASS	TRANSLATION	
								YES	NO
<i>Q.W.</i>	JP	06-268259	A	1994-09-22	JAPAN			X	
<i>Q.W.</i>	JP	07-170017	A	1995-07-04	JAPAN			X	
<i>Q.W.</i>	JP	08-213653	A	1996-08-20	JAPAN			X	

## OTHER DOCUMENTS

(Include Name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.) date, page(s), volume-issue number(s), publisher, city and/or country where published.

EXAMINER

*Q. W. H.*

DATE CONSIDERED

*9/8/04*

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